

N-Channel Power MOSFET

General Features

• $V_{DS} = 20V, I_D = 4.2A$

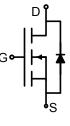
 $R_{DS(ON)}$ < 40m Ω @ V_{GS} =2.5V

 $R_{DS(ON)} < 30 \text{m} \Omega \text{@ } V_{GS} = 4.5 \text{V}$

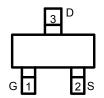
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

■MAXIMUM RATINGS

Characteristic	Symbol	Max Unit		
Drain-Source Voltage	$\mathrm{BV}_{\mathrm{DSS}}$	20	V	
Gate- Source Voltage	$ m V_{GS}$	<u>+</u> 8	V	
Drain Current (continuous)	I_{D}	4.2	A	
Drain Current (pulsed)	${ m I}_{ m DM}$	16	A	
Total Device Dissipation T _A =25°C	P_{D}	1200	mW	
Junction	Tı	150	$^{\circ}\! \mathbb{C}$	
Storage Temperature	$T_{ m stg}$	-55to+150	°C	

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ELECTRICAL CHARACTERISTICS

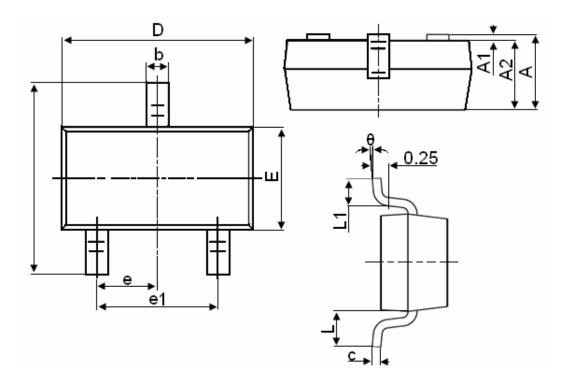
 $(T_A=25^{\circ}C$ unless otherwise noted)

(1A 25 C diffess otherwise noted)					
Characteristic	Symbol	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage $(I_D = 250uA, V_{GS}=0V)$	BVDSS	20	_	_	V
Gate Threshold Voltage (I _D = 250uA, V _{GS} = V _{DS})	V _{GS(th)}	0.45	_	1.2	V
Diode Forward Voltage Drop (I _S = 0.75A,V _{GS} =0V)	V _{SD}	_	_	1.3	V
Zero Gate Voltage Drain Current (V _{GS} =0V, V _{DS} = 16V) (V _{GS} =0V, V _{DS} = 16V, T _A =55°C)	IDSS	_	_	1 10	uA
Gate Body Leakage (V _{GS} =±8V, V _{DS} =0V)	I _{GSS}	_	_	<u>+</u> 100	nA
Static Drain-Source On-State Resistance (I _D =4.2A,V _{GS} =4.5V) (I _D =2A,V _{GS} =2.5V) (I _D =1A,V _{GS} =1.8V)	R _{DS(ON)}	_	25 30 50	30 40 60	mΩ
Input Capacitance (V _{GS} =0V, V _{DS} = 10V,f=1MHz)	CISS	_	_	650	pF
Common Source Output Capacitance (V _{GS} =0V, V _{DS} = 10V,f=1MHz)	Coss	_		150	pF
Turn-ON Time $(V_{DS}=10V, I_D=3.5A, R_{GEN}=10\Omega)$	t _(on)	_	_	20	ns
Turn-OFF Time $(V_{DS}=10V, I_D=3.5A, R_{GEN}=10\Omega)$	t(off)	_		60	ns

Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%



SOT-23 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	0.900	1.150	
A1	0.000	0.100	
A2	0.900	1.050	
b	0.300	0.500	
С	0.080	0.150	
D	2.800	3.000	
E	1.200	1.400	
E1	2.250	2.550	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.500	
θ	0°	8°	

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